## EC2500ETTSY-64.000M TR

 ECLIPTEK CORPORATION


ELECTRICAL SPECIFICATIONS

| Nominal Frequency | 64.000 MHz |
| :---: | :---: |
| Frequency Tolerance/Stability | $\pm 100 \mathrm{ppm}$ Maximum (Inclusive of all conditions: Calibration Tolerance at $25^{\circ} \mathrm{C}$, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Ouput Load Change, First Year Aging at $25^{\circ} \mathrm{C}$, Shock, and Vibration) |
| Aging at $25^{\circ} \mathrm{C}$ | $\pm 5 \mathrm{ppm} / \mathrm{year}$ Maximum |
| Operating Temperature Range | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |
| Supply Voltage | $5.0 \mathrm{Vdc} \pm 10 \%$ |
| Input Current | 50mA Maximum (No Load) |
| Output Voltage Logic High (Voh) | 2.4Vdc Minimum with TTL Load, Vdd-0.5Vdc Minimum with HCMOS Load |
| Input Current Logic High (loh) | -16mA |
| Output Voltage Logic Low (Vol) | 0.4 Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load |
| Input Current Logic Low (Iol) | 16 mA |
| Rise/Fall Time | 5 nSec Maximum (Measured at 0.4 Vdc to 2.4 Vdc with TTL Load; Measured at $10 \%$ to $90 \%$ of waveform with HCMOS Load) |
| Duty Cycle | $50 \pm 10$ (\%) (Measured at $50 \%$ of waveform with HCMOS Load or at 1.4 Vdc with TTL Load) |
| Load Drive Capability | High Drive (10TTL Load or 50pF HCMOS Load) |
| Output Logic Type | CMOS |
| Pin 1 Connection | Tri-State (High Impedance) |
| Tri-State Input Voltage (Vih and Vil) | +2.0 Vdc Minimum to enable output, +0.8 Vdc Maximum to disable output (High Impedance), No Connect to enable output. |
| RMS Phase Jitter | 1 pSec Maximum (12kHz to 20MHz offset frequency) |
| Start Up Time | 10 mSec Maximum |
| Storage Temperature Range | $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ |

ENVIRONMENTAL \& MECHANICAL SPECIFICATIONS

| Fine Leak Test | MIL-STD-883, Method 1014, Condition A |
| :--- | :--- |
| Gross Leak Test | MIL-STD-883, Method 1014, Condition C |
| Mechanical Shock | MIL-STD-202, Method 213, Condition C |
| Resistance to Soldering Heat | MIL-STD-202, Method 210 |
| Resistance to Solvents | MIL-STD-202, Method 215 |
| Solderability | MIL-STD-883, Method 2003 |
| Temperature Cycling | MIL-STD-883, Method 1010 |
| Vibration | MIL-STD-883, Method 2007, Condition A |

## EC2500ETTSY-64.000M TR

## MECHANICAL DIMENSIONS (all dimensions in millimeters)



| PIN | CONNECTION |
| :--- | :--- |
| 1 | Tri-State |
| 2 | Ground |
| 3 | Output |
| 4 | Supply Voltage |


| LINE |  |
| :--- | :--- | MARKING

## Suggested Solder Pad Layout

All Dimensions in Millimeters


All Tolerances are $\pm 0.1$

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## OUTPUT WAVEFORM \& TIMING DIAGRAM



## Test Circuit for TTL Output

| Output Load <br> Drive Capability | $\mathbf{R}_{\mathrm{L}}$ Value <br> $(\mathbf{O h m s})$ | $\mathbf{C}_{\mathrm{L}}$ Value <br> $(\mathbf{p F})$ |
| :---: | :---: | :---: |
| $10 T \mathrm{TL}$ | 390 | 15 |
| 5TTL | 780 | 15 |
| 2TTL | 1100 | 6 |
| 10LSTTL | 2000 | 15 |
| 1TTL | 2200 | 3 |

Table 1: $R_{L}$ Resistance Value and $C_{L}$ Capacitance Value Vs. Output Load Drive Capability



Note 1: An external $0.1 \mu \mathrm{~F}$ low frequency tantalum bypass capacitor in parallel with a $0.01 \mu \mathrm{~F}$ high frequency ceramic bypass capacitor close to the package ground and $V_{D D}$ pin is required.
Note 2: A low capacitance ( <12pF), 10X attenuation factor, high impedance ( $>10 \mathrm{Mohms}$ ), and high bandwidth ( $>300 \mathrm{MHz}$ ) passive probe is recommended.
Note 3: Capacitance value $C_{L}$ includes sum of all probe and fixture capacitance.
Note 4: Resistance value $R_{L}$ is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.
Note 5: All diodes are MMBD7000, MMBD914, or equivalent.

## Test Circuit for CMOS Output



Note 1: An external $0.1 \mu \mathrm{~F}$ low frequency tantalum bypass capacitor in parallel with a $0.01 \mu \mathrm{~F}$ high frequency ceramic bypass capacitor close to the package ground and $\mathrm{V}_{\mathrm{DD}}$ pin is required.
Note 2: A low capacitance ( $<12 \mathrm{pF}$ ), 10X attenuation factor, high impedance ( $>10 \mathrm{Mohms}$ ), and high bandwidth ( $>300 \mathrm{MHz}$ ) passive probe is recommended.
Note 3: Capacitance value $C_{L}$ includes sum of all probe and fixture capacitance.

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## Tape \& Reel Dimensions

Quantity Per Reel: 1,000 units

*Compliant to EIA 481A


## EC2500ETTSY-64.000M TR

## Recommended Solder Reflow Methods



High Temperature Infrared/Convection

| $\mathrm{T}_{\text {S }}$ MAX to $\mathrm{T}_{\mathrm{L}}$ (Ramp-up Rate) | $3^{\circ} \mathrm{C} /$ second Maximum |
| :---: | :---: |
| Preheat |  |
| - Temperature Minimum ( $\mathrm{T}_{\text {S }} \mathrm{MIN}$ ) | $150^{\circ} \mathrm{C}$ |
| - Temperature Typical (TS TYP) | $175^{\circ} \mathrm{C}$ |
| - Temperature Maximum (TS MAX) | $200^{\circ} \mathrm{C}$ |
| - Time ( $\mathrm{ts}_{\text {s MIN} \text { ) }}$ | 60-180 Seconds |
| Ramp-up Rate ( $\mathrm{T}_{\mathrm{L}}$ to $\mathrm{T}_{\mathrm{P}}$ ) | $3^{\circ} \mathrm{C} /$ second Maximum |
| Time Maintained Above: |  |
| - Temperature ( $\mathrm{T}_{\mathrm{L}}$ ) | $217{ }^{\circ} \mathrm{C}$ |
| - Time (t) | 60-150 Seconds |
| Peak Temperature ( $\mathrm{T}_{\mathrm{P}}$ ) | $260^{\circ} \mathrm{C}$ Maximum for 10 Seconds Maximum |
| Target Peak Temperature ( $\mathrm{T}_{\mathrm{P}}$ Target) | $250^{\circ} \mathrm{C}+0 /-5^{\circ} \mathrm{C}$ |
| Time within $5^{\circ} \mathrm{C}$ of actual peak ( $\mathrm{t}_{\mathrm{p}}$ ) | 20-40 seconds |
| Ramp-down Rate | $6^{\circ} \mathrm{C} /$ second Maximum |
| Time $25^{\circ} \mathrm{C}$ to Peak Temperature (t) | 8 minutes Maximum |
| Moisture Sensitivity Level | Level 1 |
| Additional Notes | Temperatures shown are applied to body of device. |

## EC2500ETTSY-64.000M TR

## Recommended Solder Reflow Methods



Low Temperature Infrared/Convection $240^{\circ} \mathrm{C}$

| $\mathrm{T}_{\mathrm{S}}$ MAX to $\mathrm{T}_{\mathrm{L}}$ (Ramp-up Rate) | $5^{\circ} \mathrm{C} /$ second Maximum |
| :---: | :---: |
| Preheat |  |
| - Temperature Minimum ( $\mathrm{T}_{\mathbf{S}} \mathrm{MIN}$ ) | N/A |
| - Temperature Typical ( $\mathrm{T}_{\mathrm{s}}$ TYP) | $150^{\circ} \mathrm{C}$ |
| - Temperature Maximum ( $\mathrm{T}_{\mathrm{s}} \mathrm{MAX}$ ) | N/A |
| - Time ( $\mathrm{t}_{\mathrm{s}} \mathrm{MIN}$ ) | 60-120 Seconds |
| Ramp-up Rate ( $\mathrm{L}_{\mathrm{L}}$ to $\mathrm{T}_{\mathrm{P}}$ ) | $5^{\circ} \mathrm{C} /$ second Maximum |
| Time Maintained Above: |  |
| - Temperature ( $\mathrm{T}_{\mathrm{L}}$ ) | $150^{\circ} \mathrm{C}$ |
| - Time ( $\mathrm{t}_{\mathrm{L}}$ ) | 200 Seconds Maximum |
| Peak Temperature ( $\mathrm{T}_{\mathrm{P}}$ ) | $240^{\circ} \mathrm{C}$ Maximum |
| Target Peak Temperature ( $\mathrm{T}_{\mathrm{p}}$ Target) | $240^{\circ} \mathrm{C}$ Maximum 1 Time / $230^{\circ} \mathrm{C}$ Maximum 2 Times |
| Time within $5^{\circ} \mathrm{C}$ of actual peak ( $\mathrm{t}_{\mathrm{p}}$ ) | 10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time |
| Ramp-down Rate | $5^{\circ} \mathrm{C} /$ second Maximum |
| Time $25^{\circ} \mathrm{C}$ to Peak Temperature (t) | N/A |
| Moisture Sensitivity Level | Level 1 |
| Additional Notes | Temperatures shown are applied to body of device. |

## Low Temperature Manual Soldering

$185^{\circ} \mathrm{C}$ Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

## High Temperature Manual Soldering

$260^{\circ} \mathrm{C}$ Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

